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GR 98 P 1379 D

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By: 

Date: June 15, 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 09/885,553 Confirmation No. 6319  
Applicant : Lars-Peter Heineck et al.  
Filed : June 20, 2001  
TC/A.U. : 2826  
Examiner : Johannes P. Mondt  
Title: : MOS Transistor in a Single-Transistor Memory  
Cell Having a Locally Thickened Gate Oxide

Docket No. : GR 98 P 1379 D  
Customer No. : 24131

Hon. Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**AMENDMENT**

S i r :

In response to the Office action dated March 15, 2004, please  
amend the above-identified application as follows:

**Amendments to the Claims** are reflected in the listing of  
claims which begins on page 2 of this paper.

**Remarks/Arguments** begin on page 4 of this paper.